

40V 0.7mohm N-channel SGT MOSFET
AK1G4N007GAL-T

Description:

This N channel SGT MOSFET has been designed to ultra low on-state resistance and maintain superior switching performance, especially for high efficiency power management applications.

Features:

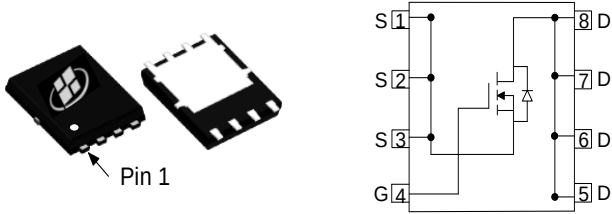
- Low $R_{DS(ON)}$
- RoHS compliant
- Halogen-free

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	40	V
$R_{DS(ON), max} @ V_{GS} = 10\text{ V}$	0.7	m Ω
I_D	345	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK1G4N007GAL-T	PDFN5X6	1G4N007GAL	Tape Reel	See the detail package information

Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{DS}	Drain - Source Voltage	40	V
I _D	Drain Current - Continuous (T _C = 25°C) ^(Note 1)	345	A
	Drain Current - Continuous (T _C = 100°C)	218	A
I _{DM}	Drain Current - Pulsed ^(Note 2)	1380	A
V _{GS}	Gate - Source Voltage	± 20	V
E _{AS}	Single Pulsed Avalanche Energy ^(Note 3)	702	mJ
P _D	Power Dissipation (T _C = 25°C)	139	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction - to - Case, Steady State	0.9	°C/W
R _{θJA}	Thermal Resistance, Junction - to - Ambient, Steady State ^(Note 4)	45	°C/W

Notes:

1. The max drain current rating is silicon limited
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 0.5 mH, V_{DD} = 20 V, I_{AS} = 53 A, R_g = 50 Ω, Starting T_J = 25 °C
4. Mount on minimum PCB layout

Electrical Characteristics ($T_j = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
V _{(BR)DSS}	Drain - Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 40 V, V _{GS} = 0 V,			1	μA
I _{GSS}	Gate Leakage Current	V _{GS} = ± 20 V, V _{DS} = 0 V			±100	nA
V _{GS(th)}	Gate Threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.8	3	V
R _{DS(ON)}	Drain - Source on - state resistance	V _{GS} = 10 V, I _D = 50 A		0.59	0.7	mΩ
		V _{GS} = 4.5 V, I _D = 50 A		0.92	1.45	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz		6760		pF
C _{oss}	Output Capacitance			2700		pF
C _{rss}	Reverse Transfer Capacitance			67		pF
R _g	Gate Resistance	f = 1 MHz		1.85		Ω
Switching Characteristics						
t _{d(on)}	Turn On Delay Time	V _{DD} = 20 V , R _L = 1 Ω, V _{GS} = 10 V, R _G = 1.1 Ω		15		ns
t _r	Rise Time			38		ns
t _{d(off)}	Turn Off Delay Time			46		ns
t _f	Fall Time			14		ns
Q _g	Total Gate Charge	V _{DD} = 20 V , I _D = 50 A, V _{GS} = 10 V		92		nC
Q _{gs}	Gate - Source Charge			18		nC
Q _{gd}	Gate - Drain Charge			16		nC
Drain - Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Body - Diode Forward Current				345	A
I _{SM}	Maximum Pulsed Body - Diode Forward Current				1380	A
V _{SD}	Diode Forward Voltage	V _{GS} = 0 V, I _S = 50 A		0.75		V
t _{rr}	Reverse recovery time	V _{DD} = 20 V, I _D = 20 A, di/dt = 100 A/μs		85		ns
Q _{rr}	Reverse recovery charge			135		nC
I _{rrm}	Peak Reverse Recovery Current			2.6		A

Electrical Characteristics Diagrams

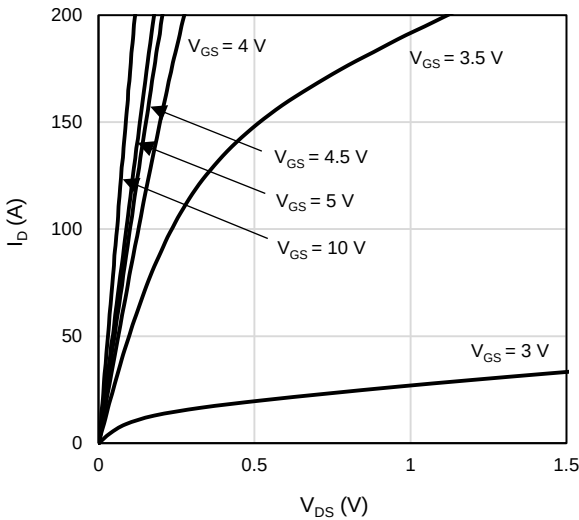


Figure 1: On-Region Characteristics

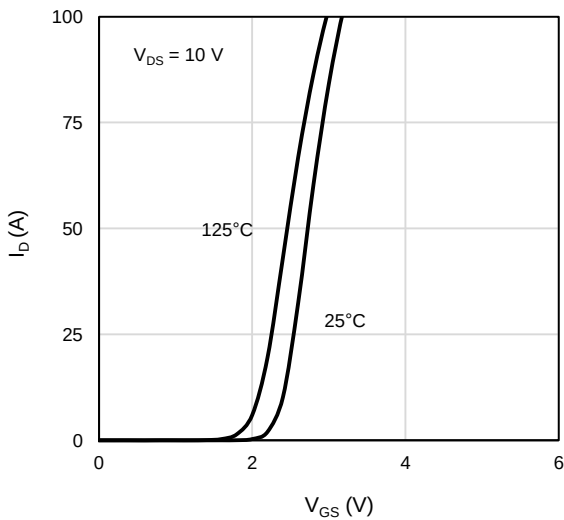


Figure 2: Transfer Characteristics

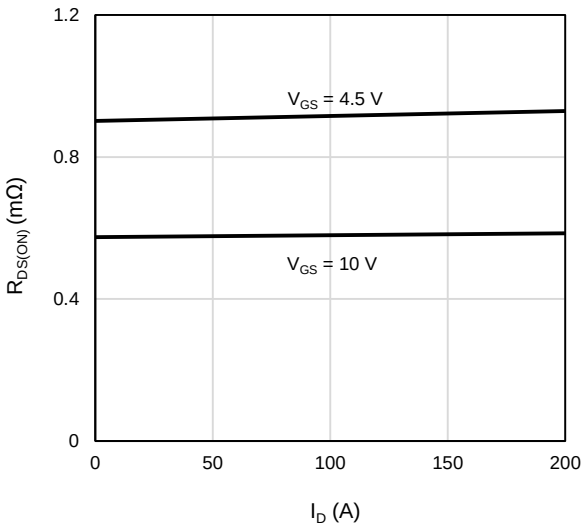


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

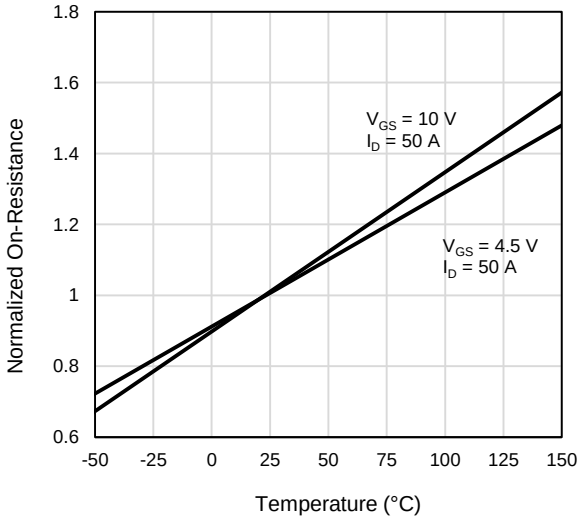


Figure 4: On-Resistance vs. Junction Temperature

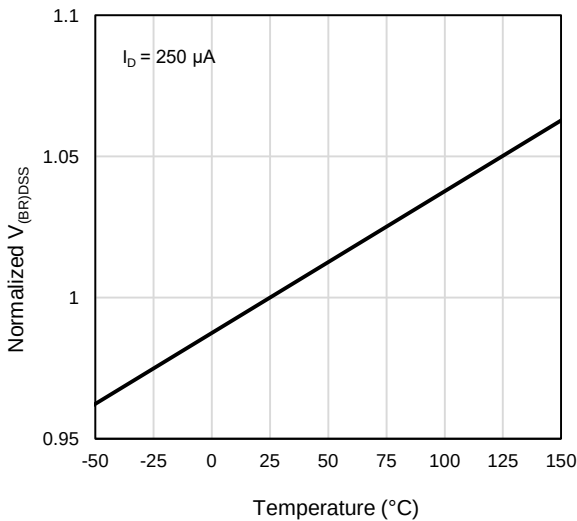


Figure 5: Breakdown Voltage vs. Junction Temperature

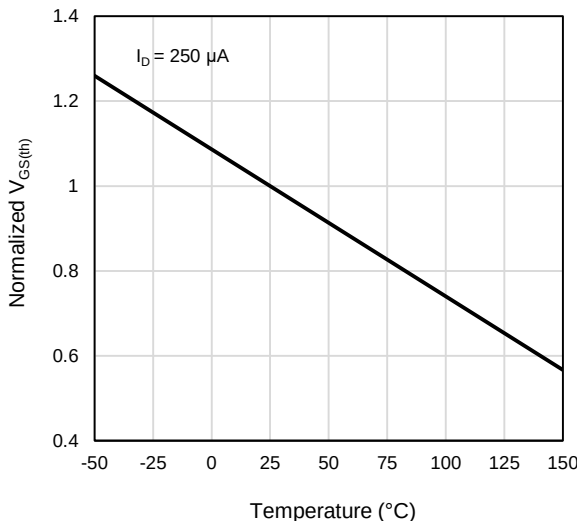


Figure 6: Threshold Voltage vs. Junction Temperature

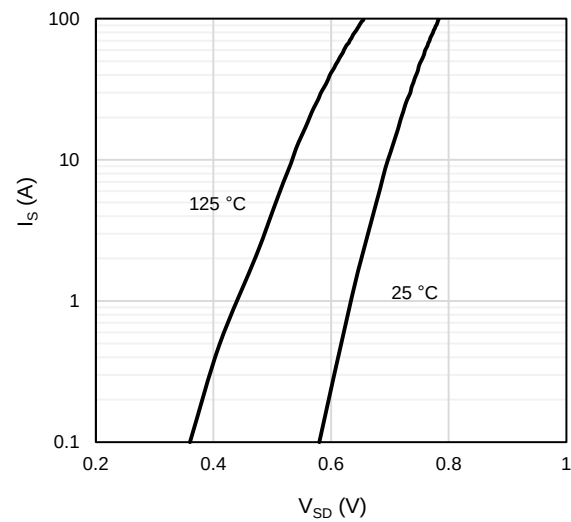


Figure 7: Body-Diode Characteristics

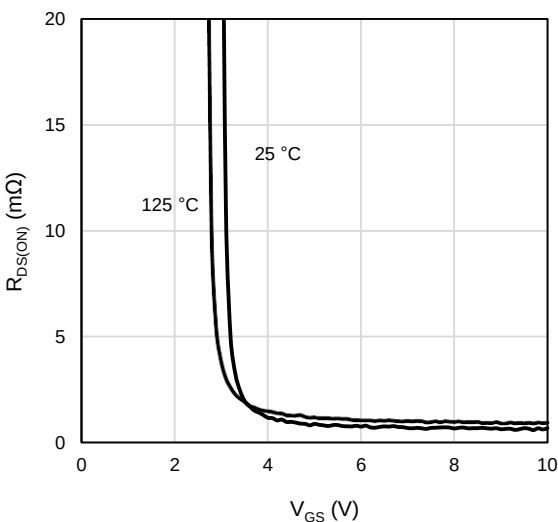


Figure 8: On-Resistance vs. Gate-Source Voltage

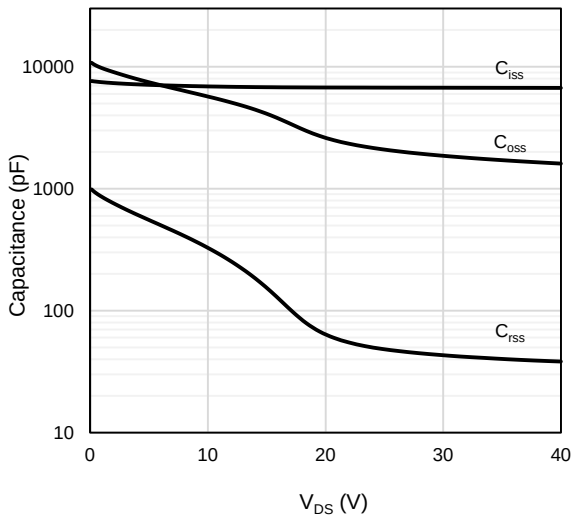


Figure 9: Capacitance Characteristics

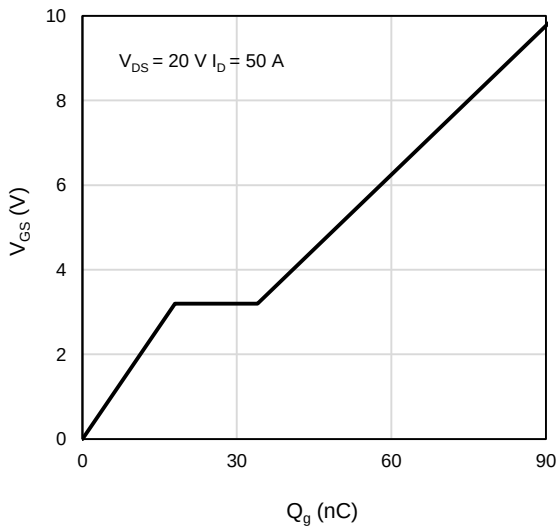


Figure 10: Gate-Charge Characteristics

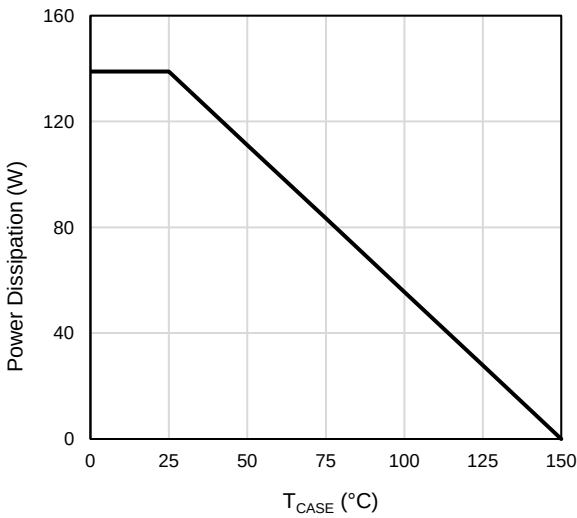


Figure 11: Power De-rating

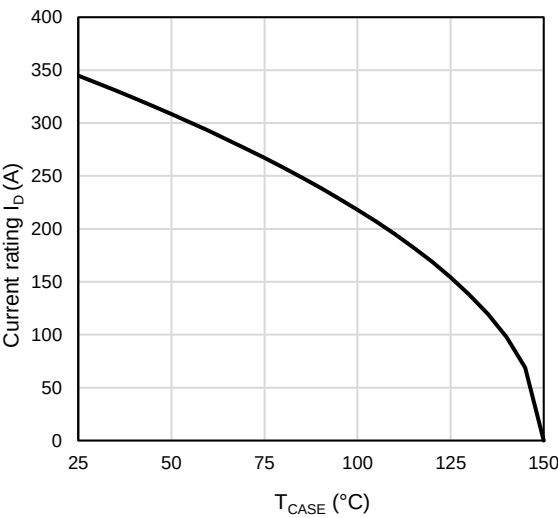


Figure 12: Current De-rating

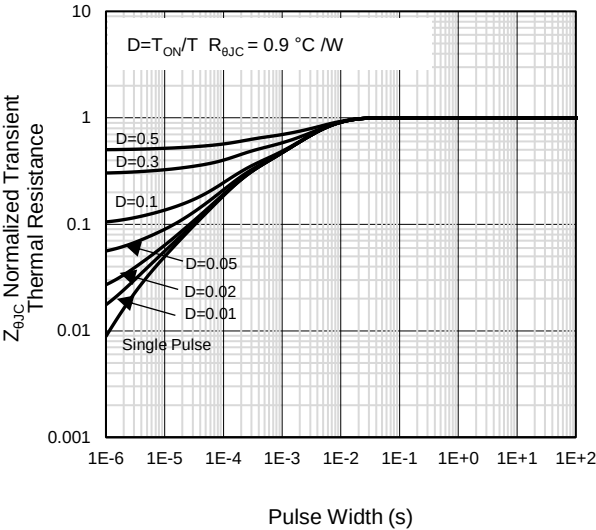


Figure 13: Normalized Maximum Transient Thermal Impedance

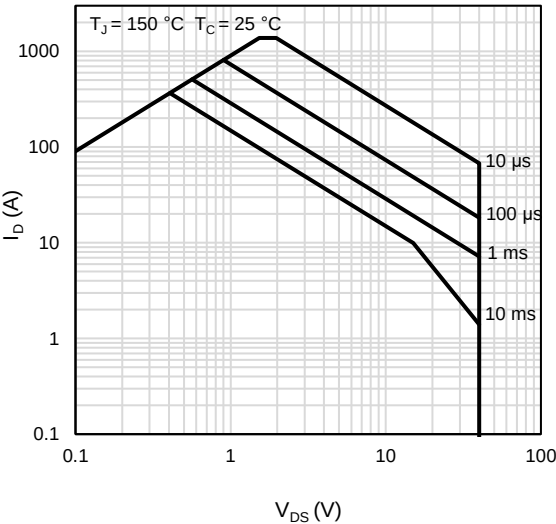
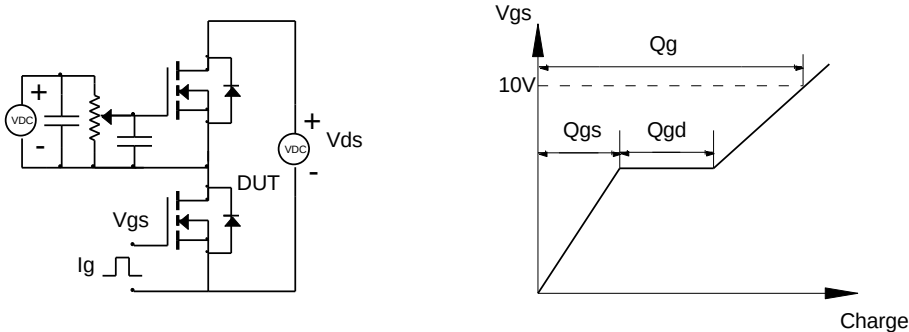


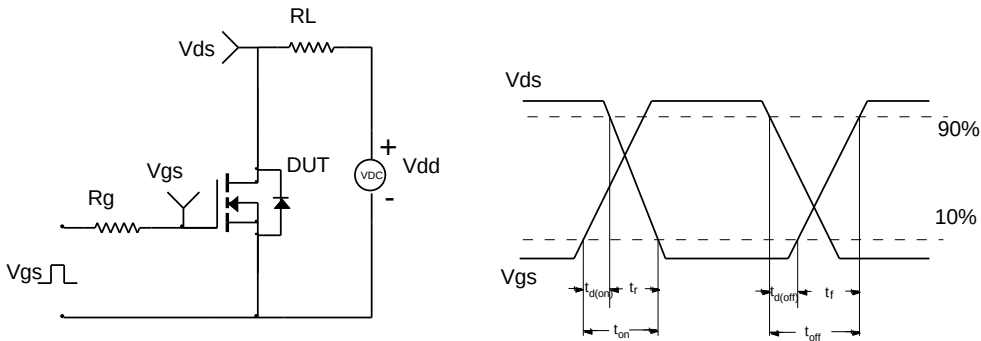
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

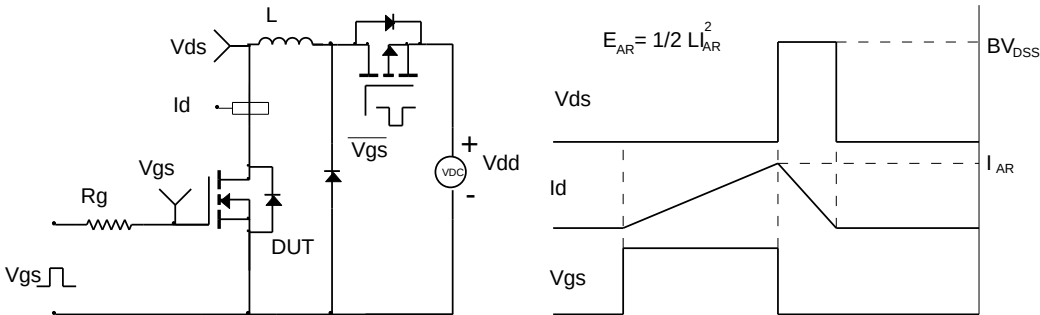
Gate Charge Test Circuit & Waveform



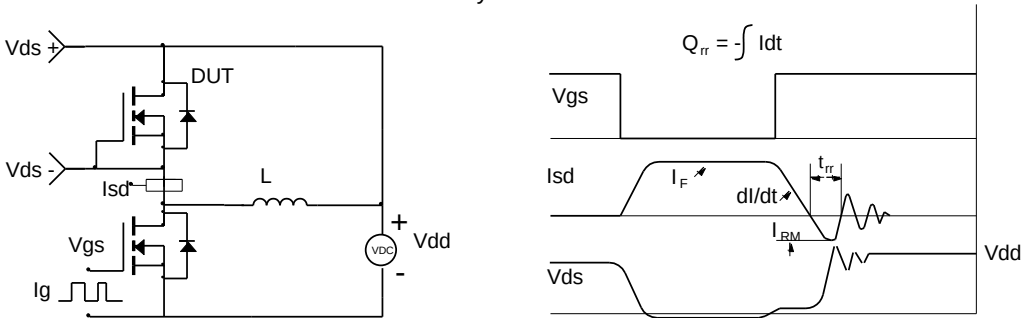
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Released	Remark
Rev.1.0	2025	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.